

Silicon NPN Power Transistors

2SC4793

DESCRIPTION

- With TO-220F package
- Complement to type 2SA1837
- High transition frequency

APPLICATIONS

- Power amplifier applications
- Driver stage amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

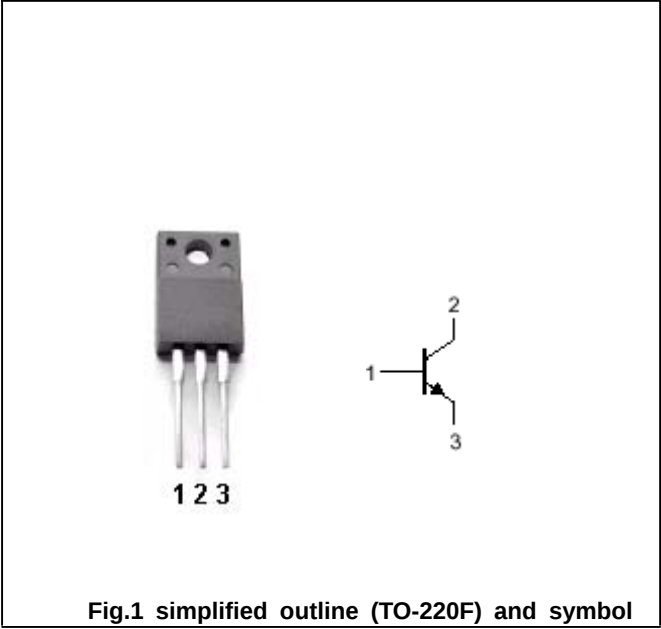


Fig.1 simplified outline (TO-220F) and symbol

Absolute maximum ratings (Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	230	V
V _{CEO}	Collector-emitter voltage	Open base	230	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		1	A
I _B	Base current		0.1	A
P _C	Collector dissipation	T _C =25	20	W
P _C	Collector dissipation	T _a =25	2.0	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

Silicon NPN Power Transistors

2SC4793

CHARACTERISTICS**T_j=25** unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO}	Collector-emitter breakdown voltage	I _C =10mA ; I _B =0	230			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =0.5A I _B =50mA			1.5	V
V _{BE}	Base-emitter voltage	I _C =0.5A ; V _{CE} =5V			1.0	V
I _{CBO}	Collector cut-off current	V _{CB} =230V I _E =0			1.0	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			1.0	μ A
h _{FE}	DC current gain	I _C =0.1A ; V _{CE} =5V	100		320	
C _{OB}	Output capacitance	I _E =0; V _{CB} =10V;f=1MHz		20		pF
f _T	Transition frequency	I _C =0.1A ; V _{CE} =10V		100		MHz

Silicon NPN Power Transistors

2SC4793

PACKAGE OUTLINE

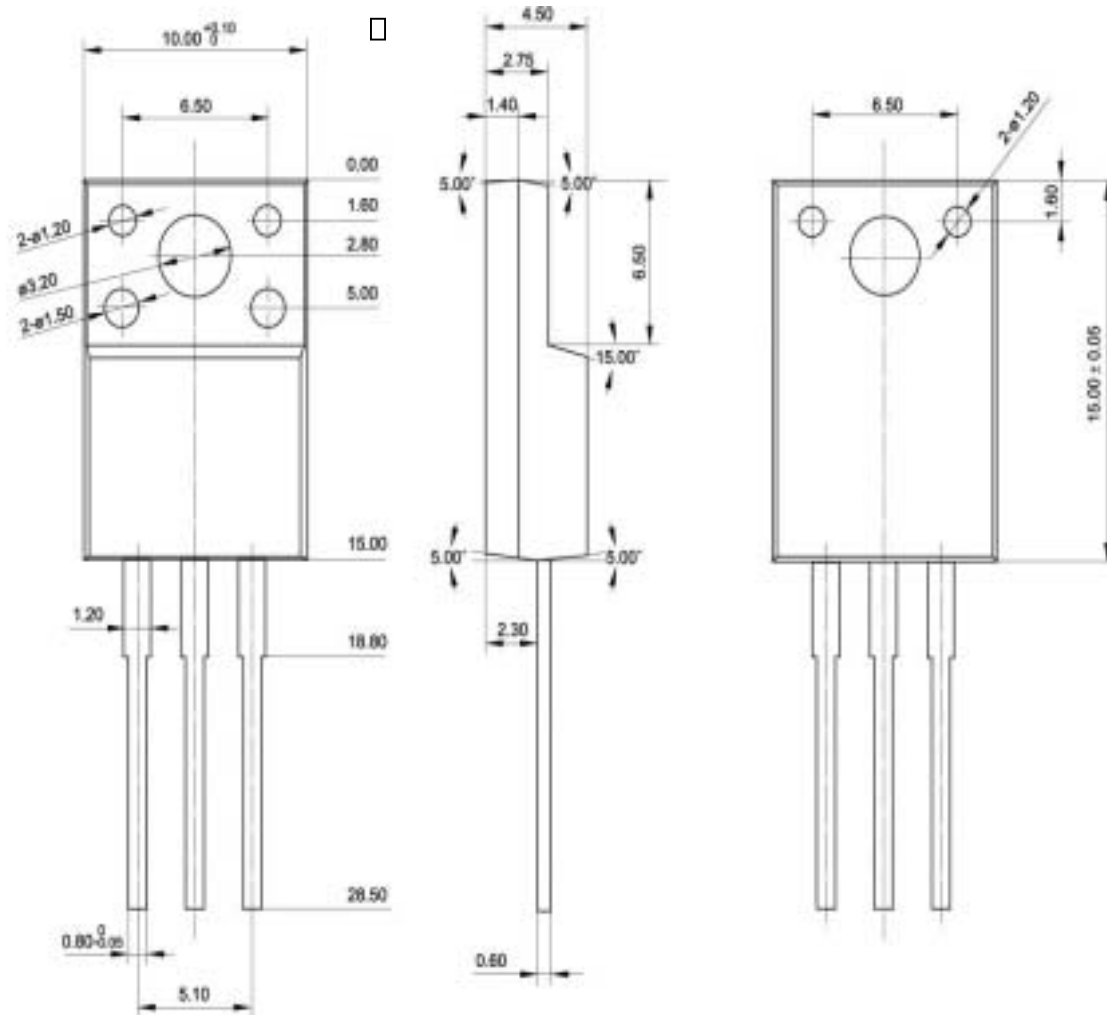


Fig.2 Outline dimensions